

SANYO	No.1943A	2SA1392/2SC3383
		PNP/NPN Epitaxial Planar Silicon Transistors
		AF Amp Applications

Features

- . Adoption of FBET process
- . AF amp

(): 2SA1392

Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V _{CB0}	(-)60	V
Collector to Emitter Voltage	V _{CE0}	(-)50	V
Emitter to Base Voltage	V _{EBO}	(-)6	V
Collector Current	I _C	(-)200	mA
Collector Current (Pulse)	I _{CP}	(-)400	mA
Collector Dissipation	P _C	400	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

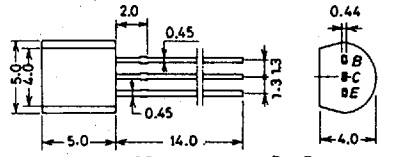
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} =(-)40V, I _E =0			(-)0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)5V, I _C =0			(-)0.1	μA
DC Current Gain	h _{FE} (1)	V _{CE} =(-)6V, I _C =(-)1mA	100*		560*	
	h _{FE} (2)	V _{CE} =(-)6V, I _C =(-)0.1mA	70			
Gain-Bandwidth Product	f _T	V _{CE} =(-)6V, I _C =(-)10mA		250		MHz
				(200)		MHz
C-E Saturation Voltage	V _{CE(sat)}	I _C =(-)100mA, I _B =(-)10mA			(-)0.3	V
B-E Saturation Voltage	V _{BE(sat)}	I _C =(-)100mA, I _B =(-)10mA			(-)1.0	V
Output Capacitance	c _{ob}	V _{CB} =(-)6V, f=1MHz		2.7		pF
				(3.7)		pF
C-B Breakdown Voltage	V(BR)CBO	I _C =(-)10μA, I _E =0	(-)60			V
C-E Breakdown Voltage	V(BR)CEO	I _C =(-)1mA, R _{BE} =∞	(-)50			V
E-B Breakdown Voltage	V(BR)EBO	I _E =(-)10μA, I _C =0	(-)6			V

*: The 2SA1392/2SC3383 are classified by 1mA h_{FE} as follows:

100	R	200	140	S	280	200	T	400	280	U	560
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Case Outline 2003A
(unit:mm)

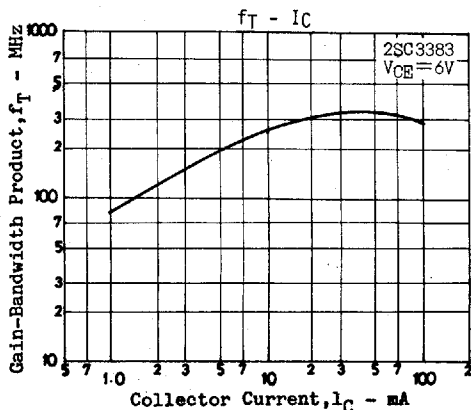
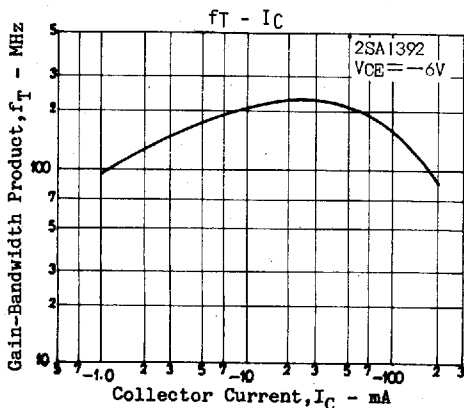
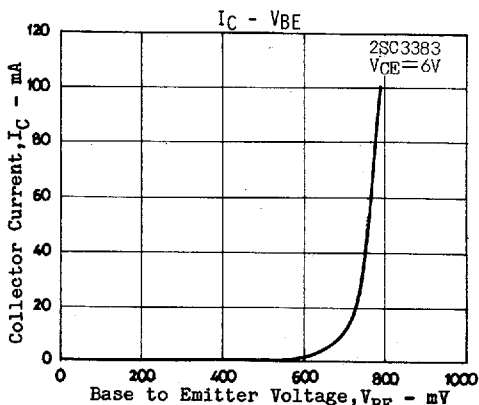
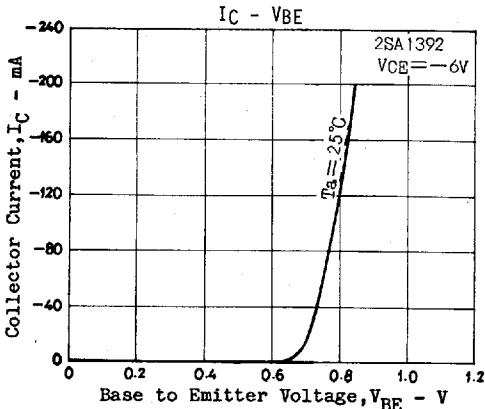
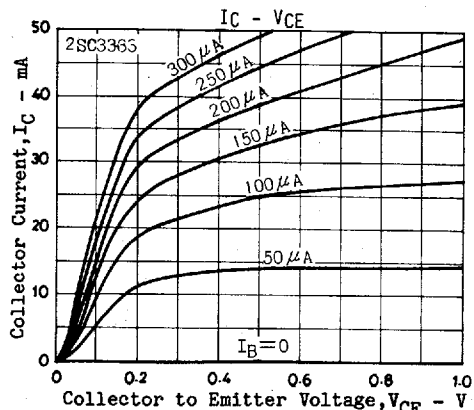
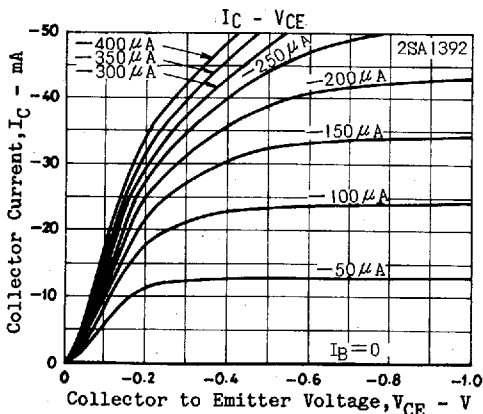
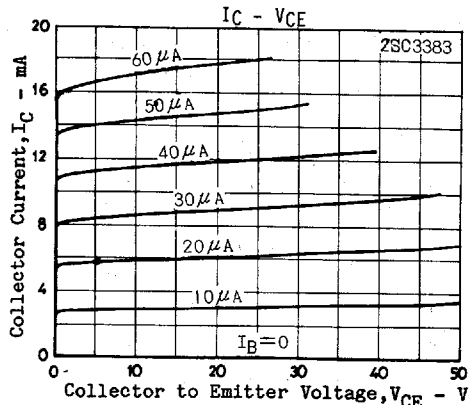
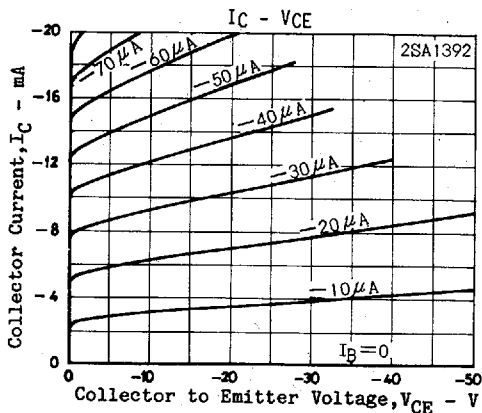


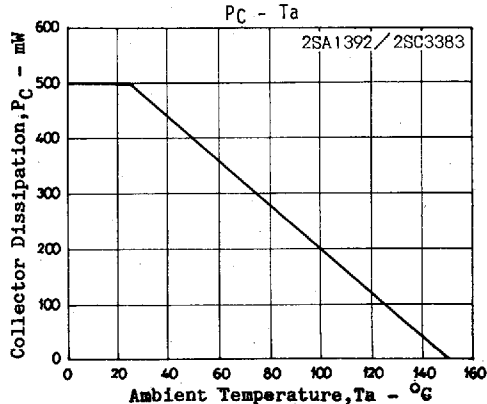
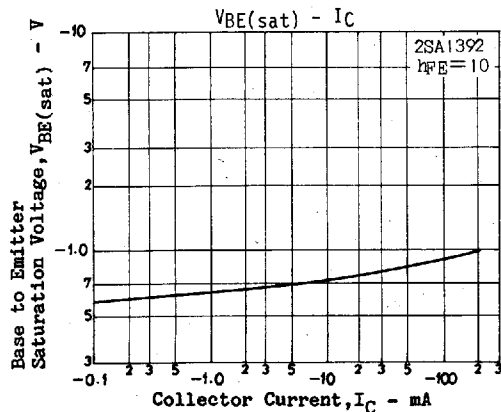
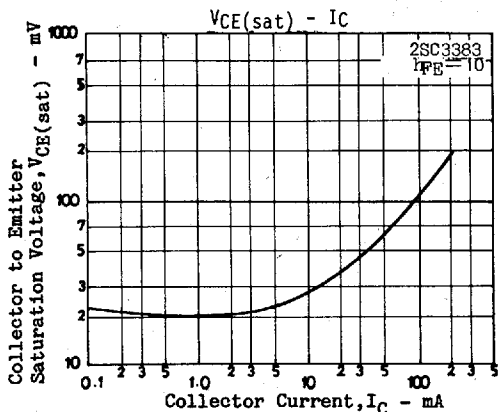
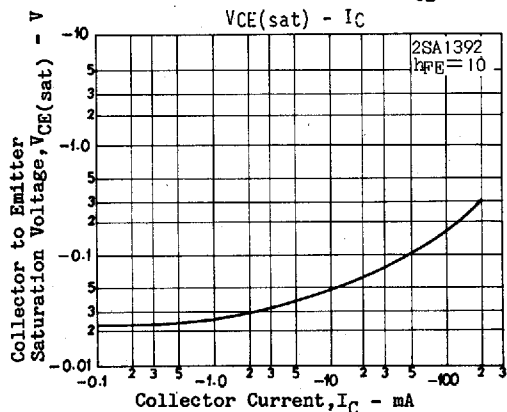
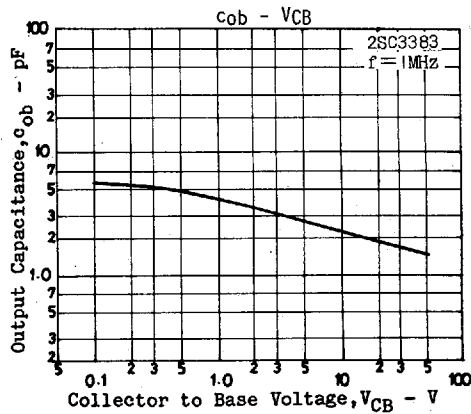
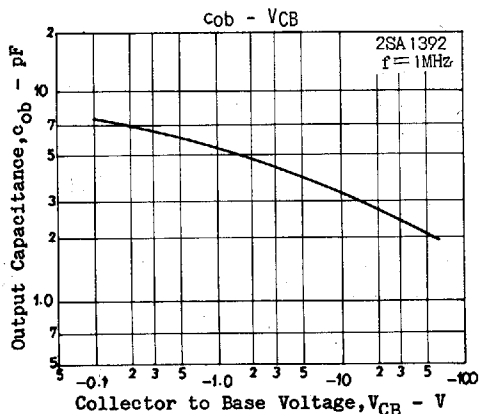
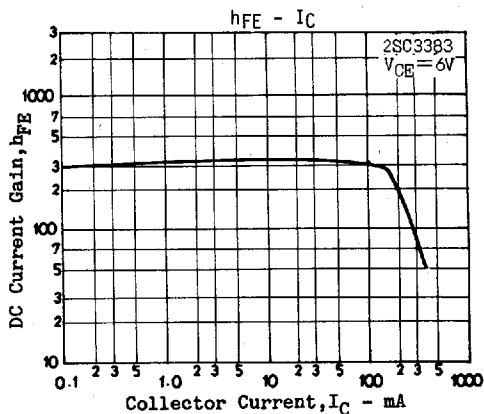
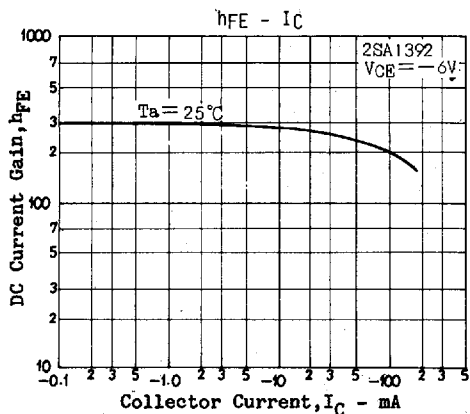
JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

B. Base
C. Collector
E. Emitter

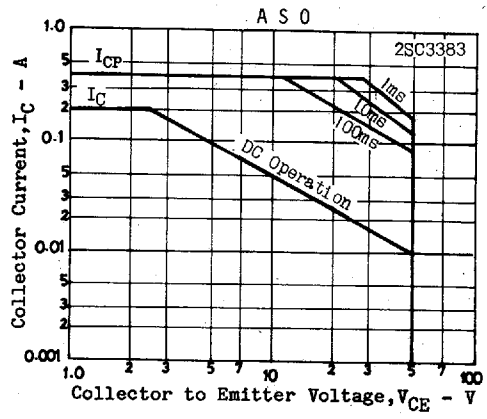
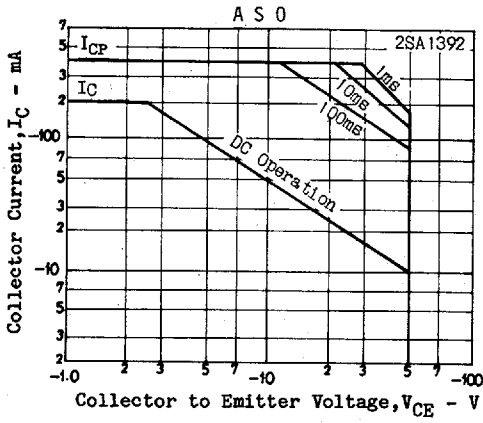
Specifications and information herein are subject to change without notice.

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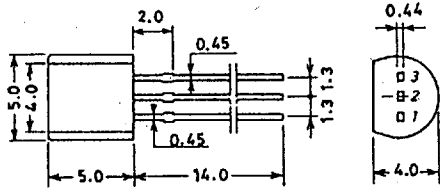
2SA1392/2SC3383



CASE OUTLINES OF LEAD FORMED SMALL SIGNAL TRANSISTORS

- All of Sanyo lead formed small signal transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

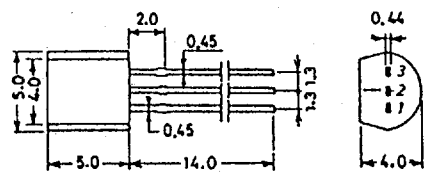
Case Outline 2003A/2003B (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1 : Emitter
2 : Collector
3 : Base

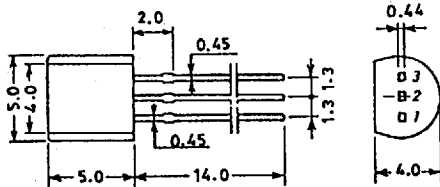
Case Outline 2019A/2019B (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1 : Source
2 : Gate
3 : Drain

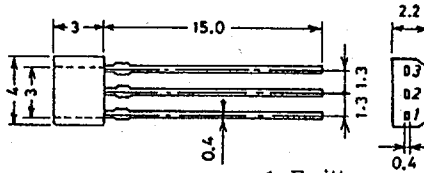
Case Outline 2004A (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1 : Base
2 : Emitter
3 : Collector

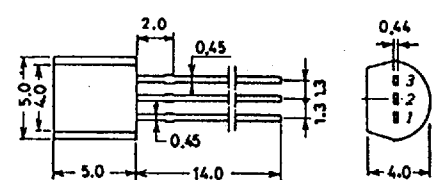
Case Outline 2033 (unit : mm)



1 : Emitter
2 : Collector
3 : Base

SANYO : SPA

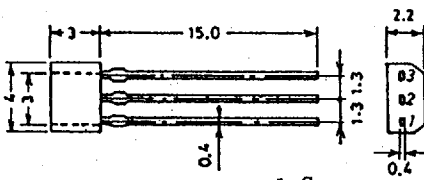
Case Outline 2005A (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1 : Drain
2 : Source
3 : Gate

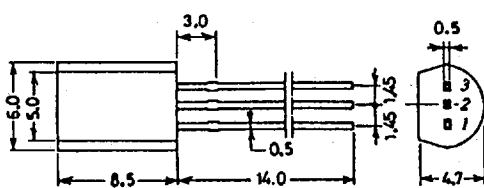
Case Outline 2034/2034A (unit : mm)



1 : Source
2 : Gate
3 : Drain

SANYO : SPA

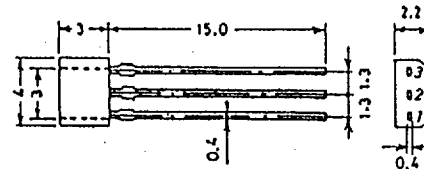
Case Outline 2006A (unit : mm)



EIAJ : SC-51
SANYO : MP

1 : Emitter
2 : Collector
3 : Base

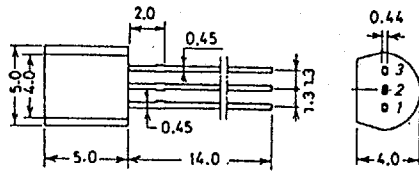
Case Outline 2040 (unit : mm)



1 : Drain
2 : Source
3 : Gate

SANYO : SPA

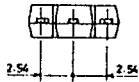
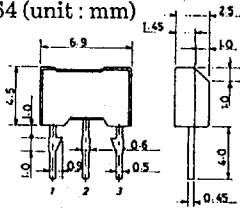
Case Outline 2061 (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1: Emitter
2: Base
3: Collector

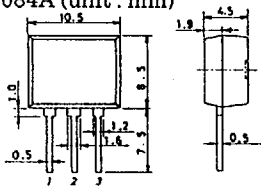
Case Outline 2064 (unit : mm)



1: Emitter
2: Collector
3: Base

SANYO : NMP

Case Outline 2084A (unit : mm)



1: Emitter
2: Collector
3: Base

SANYO : FLP